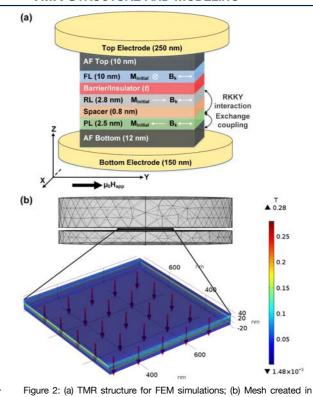


# Modelling of Spintronic Nanodevices for Neuromorphic Sensing Chips

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#### **OVERVIEW**

We developed a finite element method-based model of an MgO-barrier TMR device in COMSOL Multiphysics® for integrated circuit designers to implement them in a hybrid spintronic-CMOS system [1]. (a) **CADENCE Environment** TMR Sensor Analogue mpact Model Front-End Verilog A **Device Modelling** COMSOL (b) 2000 1950 [Ohm] Resistance 1900 Free Lave Barrie 1850 Reference Lay R 0 10 15 10 -5



COMSOL software and then zooming in on the MTJ

Figure 1: Proposed idea for extracting data from COMSOL Multiphysics® to Cadence® environment.

Magnetic Field [kA/m]

### SIMULATION RESULTS

These results are consistent with previous experimental results of fabricated MTJ samples reported in the literature, which show a higher TMR ratio and better small range linearization.

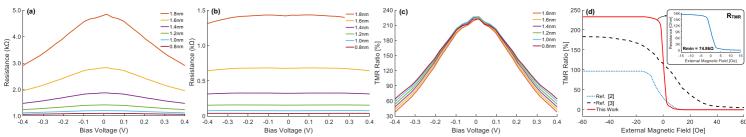


Figure 3: Effect of  $t_{ox}$  on (a) the anti-parallel and (b) the parallel resistances of the TMR sensor with different bias voltages. (c) Effect of tox on TMR ratio with different bias voltages. (d) TMR response compared to [2].

## **CONCLUSION AND FUTURE WORK**

A novel TMR compact model was developed using *Verilog-A* extracted from accurate 3D FEM simulation. The effect of the insulator layer's thickness of TMR performance was presented for supporting spintronic-CMOS magnetic sensor development. A TMR ratio of 233% with 10 mV power supply was obtained from *COMSOL* and was verified *Verilog-A* model in Cadence.

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